



TS13003HV

High Voltage NPN Transistor

TO-92



Pin assignment:
 1. Emitter
 2. Collector
 3. Base

BV_{CBO} = 530V
BV_{CEO} = 900V
I_c = 1.5A
V_{CE(SAT)}, = 0.5V @ I_c / I_b = 0.5A / 0.1A

Features

- ◊ High voltage.
- ◊ High speed switching

Structure

- ◊ Silicon triple diffused type.
- ◊ NPN silicon transistor

Ordering Information

Part No.	Packing	Package
TS13003HVCT B0	Bulk Pack	TO-92
TS13003HVCT A3	Ammo Pack	TO-92

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Collector-Base Voltage		V _{CBO}	900V	V
Collector-Emitter Voltage		V _{CEO}	530V	V
Emitter-Base Voltage		V _{EBO}	10	V
Collector Current	DC	I _c	1.5	A
	Pulse		3	
Collector Power Dissipation		P _D	0.6	W
Operating Junction Temperature		T _J	+150	°C
Operating Junction and Storage Temperature Range		T _{STG}	-55 to +150	°C

Note: 1. Single pulse, Pw = 300uS, Duty <= 2%

Electrical Characteristics (Ta = 25 °C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Collector-Base Voltage	I _C = 10mA, I _B = 0	BV _{CBO}	900	--	--	V
Collector-Emitter Breakdown Voltage	I _C = 10mA, I _E = 0	BV _{CEO}	530	--	--	V
Emitter-Base Breakdown Voltage	I _E = 1mA, I _C = 0	BV _{EBO}	9	--	--	V
Collector Cutoff Current	V _{CB} = 800V, I _E = 0	I _{CBO}	--	--	10	uA
Emitter Cutoff Current	V _{EB} = 10V, I _C = 0	I _{EBO}	--	--	0.5	uA
Collector-Emitter Saturation Voltage	I _C / I _B = 1.5A / 0.5A I _C / I _B = 0.5A / 0.1A	V _{CE(SAT)1} V _{CE(SAT)2}	-- --	-- --	2.5 0.8	V
DC Current Gain	V _{CE} = 10V, I _C = 10uA V _{CE} = 10V, I _C = 0.4A V _{CE} = 10V, I _C = 1.0A	h _{FE}	15 20 6	-- -- --	40 40 40	
Frequency	V _{CE} = 10V, I _C = 0.1A	f _T	4	--	--	MHz
Output Capacitance	V _{CB} = 10V, f = 0.1MHz	C _{ob}	--	21	--	pF
Turn On Time	V _{CC} = 125V, I _C = 1A, I _{B1} = 0.2A, I _{B2} = - 0.2A,	t _{ON}	--	1.1	--	uS
Storage Time		t _{STG}	--	--	4	uS
Fall Time	R _L = 125ohm	t _f	--	--	0.7	uS

Note : pulse test: pulse width <=300uS, duty cycle <=2%

Electrical Characteristics Curve

Figure 1. Static Characteric

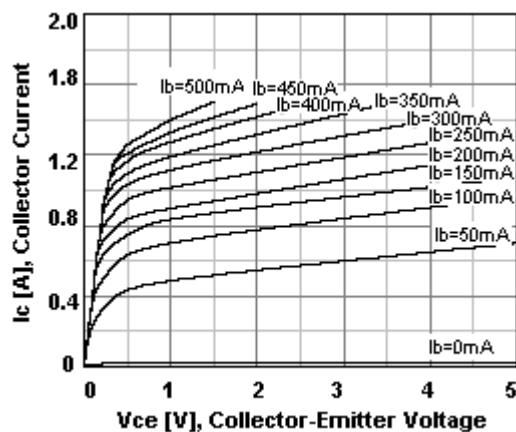


Figure 2. DC Current Gain

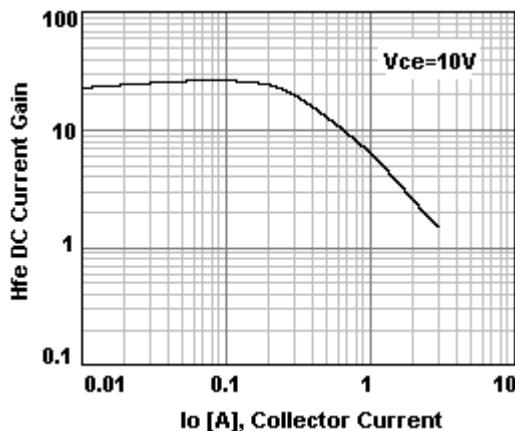


Figure 3. $V_{ce(sat)}$ v.s. $V_{be(sat)}$

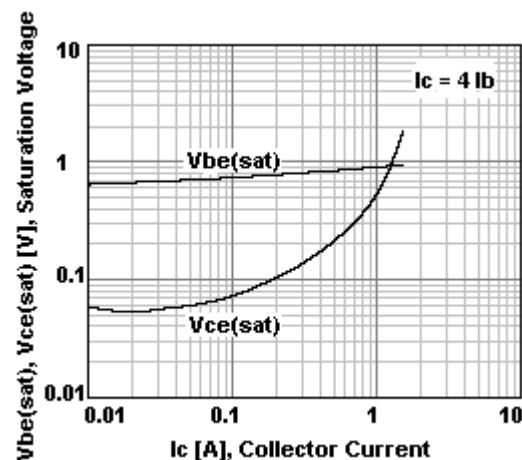


Figure 4. Switching Time

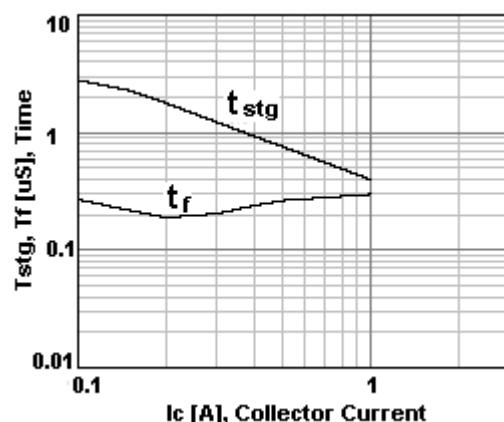


Figure 5. Safe Operating Area

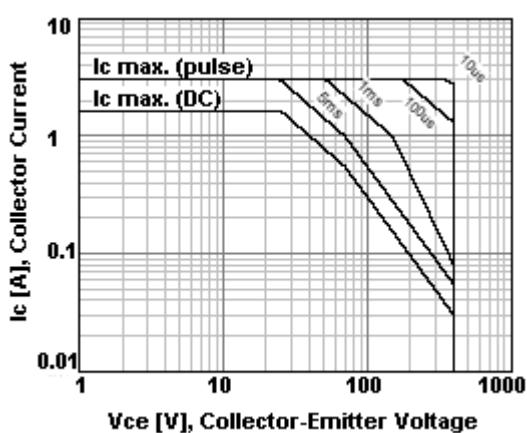
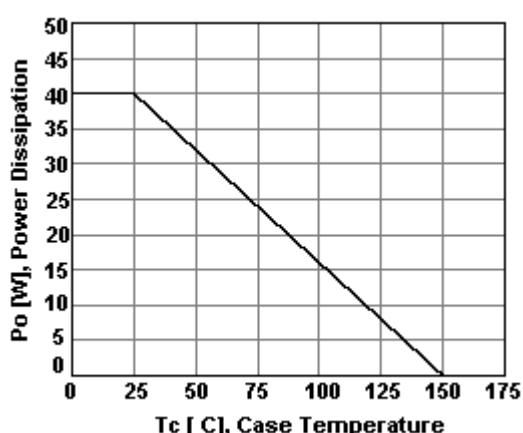
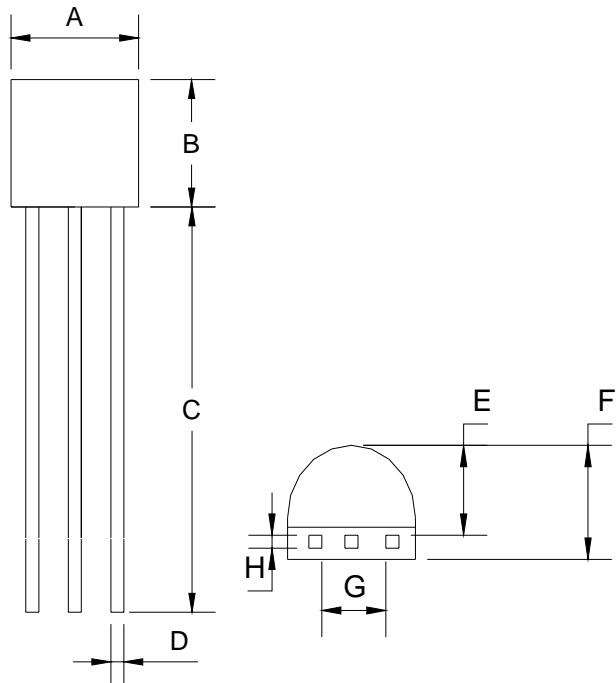


Figure 6. Power Derating



TO-92 Mechanical Drawing



TO-92 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	14.30(typ)		0.563(typ)	
D	0.43	0.49	0.017	0.019
E	2.19	2.81	0.086	0.111
F	3.30	3.70	0.130	0.146
G	2.42	2.66	0.095	0.105
H	0.37	0.43	0.015	0.017